

## عنوان مقاله:

Simulation of the Process of LDMOS Transistor Manufacture and Optimizing it to Increase the Current of Work

## محل انتشار:

مجله مهندسی برق مجلسی، دوره 11، شماره 4 (سال: 1396)

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## خلاصه مقاله:

This paper presents the simulation of the process of LDMOS transistor manufacturing by using Silvaco software and by relying on the ability of calculating the basic parameters of transistor dependencies, focusing on the optimization of the manufacturing process in order to increase the current of work. The simulation of manufacturing process of this type of transistor which is a base for its real manufacturing is of the utmost importance. By using this simulation and reviewing each parameter, we can achieve the optimized manufacturing process by focusing each basic parameter and by paying attention to its required application. In order to design, we first define the construction procedures and the necessary processes using the Athena simulator, and then we use the Atlas device simulator to acquire electrical parameters.

## کلمات کلیدی:

LDMOS transistor, en, Current operating point, Threshold voltage, Cut-off Frequency, Transconductance, Breakdown voltage

## لینک ثابت مقاله در پایگاه سیویلیکا:

<https://civilica.com/doc/1617520>

